

Silicon NPN Power Transistor

DESCRIPTION

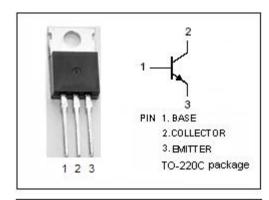
- Collector-Emitter Breakdown Voltage-:V_{(BR)CEO}= 150V(Min)
- Wide Area of Safe Operation
- Complement to Type 2SA940

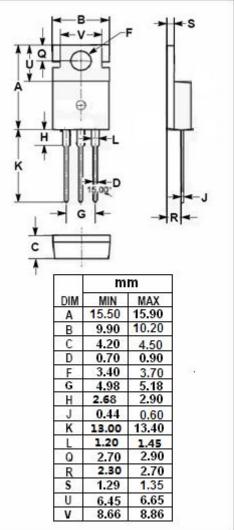
APPLICATIONS

- Power amplifier applications.
- · Vertical output applications.

ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT	
V _{CBO}	Collector-Base Voltage	150	V	
Vceo	Collector-Emitter Voltage	150	V	
V_{EBO}	Emitter-Base Voltage	5	V	
Ic	Collector Current-Continuous	1.5	А	
I _B	Base Current-Continuous	0.5	Α	
P _C	Collector Power Dissipation @ T _a =25°C	1.5	W	
	Collector Power Dissipation @ T _C =25°C	25		
TJ	Junction Temperature	Temperature 150		
T _{stg}	Storage Temperature Range	-55~150	$^{\circ}$	





Ordering Information

Product	Package	Packaging
2SC2073T1TL	TO-220C	Tube

V01 1



ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
Collector-Emitter Saturation Voltage	I _C = 500mA; I _B = 50mA			1.5	V
Base-Emitter On Voltage	I _C = 500mA ; V _{CE} = 10V			0.85	V
Collector Cutoff Current	V _{CB} = 120V ; I _E = 0			10	μА
Emitter Cutoff Current	V _{EB} = 5V; I _C = 0			10	μА
DC Current Gain	I _C = 500mA ; V _{CE} = 10V	40		140	
Output Capacitance	I _E = 0; V _{CB} = 10V; f _{test} = 1MHz		35		pF
Current-Gain—Bandwidth Product	I _C = 500mA; V _{CE} = 10V		4		MHz
	PARAMETER Collector-Emitter Saturation Voltage Base-Emitter On Voltage Collector Cutoff Current Emitter Cutoff Current DC Current Gain Output Capacitance	PARAMETERCONDITIONSCollector-Emitter Saturation Voltage $I_C = 500 \text{mA}$; $I_B = 50 \text{mA}$ Base-Emitter On Voltage $I_C = 500 \text{mA}$; $V_{CE} = 10 \text{V}$ Collector Cutoff Current $V_{CB} = 120 \text{V}$; $I_E = 0$ Emitter Cutoff Current $V_{EB} = 5 \text{V}$; $I_C = 0$ DC Current Gain $I_C = 500 \text{mA}$; $V_{CE} = 10 \text{V}$ Output Capacitance $I_E = 0$; $V_{CB} = 10 \text{V}$; $f_{test} = 1 \text{MHz}$	PARAMETERCONDITIONSMINCollector-Emitter Saturation Voltage $I_C = 500 \text{mA}$; $I_B = 50 \text{mA}$ Base-Emitter On Voltage $I_C = 500 \text{mA}$; $V_{CE} = 10 \text{V}$ Collector Cutoff Current $V_{CB} = 120 \text{V}$; $I_E = 0$ Emitter Cutoff Current $V_{EB} = 5 \text{V}$; $I_C = 0$ DC Current Gain $I_C = 500 \text{mA}$; $V_{CE} = 10 \text{V}$ Output Capacitance $I_E = 0$; $V_{CB} = 10 \text{V}$; $f_{test} = 1 \text{MHz}$	PARAMETERCONDITIONSMINTYP.Collector-Emitter Saturation Voltage $I_C = 500 \text{mA}$; $I_B = 50 \text{mA}$	PARAMETERCONDITIONSMINTYP.MAXCollector-Emitter Saturation Voltage $I_{C}=500\text{mA}$; $I_{B}=50\text{mA}$ 1.5Base-Emitter On Voltage $I_{C}=500\text{mA}$; $V_{CE}=10\text{V}$ 0.85Collector Cutoff Current $V_{CB}=120\text{V}$; $I_{E}=0$ 10Emitter Cutoff Current $V_{EB}=5\text{V}$; $I_{C}=0$ 10DC Current Gain $I_{C}=500\text{mA}$; $V_{CE}=10\text{V}$ 40140Output Capacitance $I_{E}=0$; $V_{CB}=10\text{V}$; $f_{test}=1\text{MHz}$ 35

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